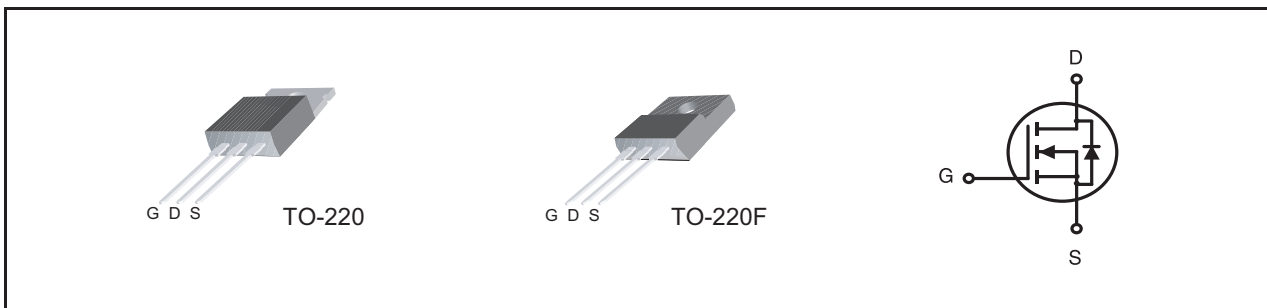


**400V N-Channel Planar MOSFET****PRODUCT SUMMARY**

V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DS(ON)</sub> (mΩ) Max
400V	10A	0.55 @ V <sub>GS</sub> =10V, I <sub>D</sub> =5A

**FEATURES**

- Fast Switching.
- 100% Avalanche Rated.

**ABSOLUTE MAXIMUM RATINGS** (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	SDP740	SDF740	Units	
V <sub>DSS</sub>	Drain-Source Voltage	400		V	
V <sub>GS</sub>	Gate-Source Voltage	±30		V	
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> =25°C	10	10 *	A
		T <sub>C</sub> =100°C	6.3	6.3 *	A
I <sub>DM</sub>	Pulsed Drain Current, V <sub>GS</sub> =10V <sup>a</sup>	40	40 *	A	
E <sub>AS</sub>	Single Pulse Avalanche Energy <sup>b</sup>	300		mJ	
dv/dt	Peak Diode Recovery Energy <sup>c</sup>			V/ns	
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> =25°C	125	42	W
	Linear Derating Factor	T <sub>C</sub> >25°C	1	0.34	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to 150		°C	

\* Drain current limited by maximum junction temperature

**THERMAL CHARACTERISTICS**

Symbol	Parameter	SDP740	SDF740	Units
R <sub>θ JC</sub>	Thermal Resistance, Junction-to-Case	1	3	°C/W
R <sub>θ JA</sub>	Thermal Resistance, Junction-to-Ambient	62.5	62.5	°C/W

# SDP/F740

Preliminary

## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	400			V
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =250uA		0.54		V/°C
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>DS</sub> =400V, V <sub>GS</sub> =0V			20	uA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>DS</sub> =0V, V <sub>GS</sub> =30V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>DS</sub> =0V, V <sub>GS</sub> =-30V			-100	nA
<b>ON CHARACTERISTICS</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	2.0		4.0	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =10V, I <sub>D</sub> =5A <sup>d</sup>			0.55	ohm
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =15V, I <sub>D</sub> =5A <sup>d</sup>			20	S
<b>DYNAMIC CHARACTERISTICS</b>						
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V f=1.0MHz		882		pF
C <sub>OSS</sub>	Output Capacitance			263		pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			89		pF
<b>SWITCHING CHARACTERISTICS</b>						
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =200V I <sub>D</sub> =10A R <sub>G</sub> =10 ohm, R <sub>D</sub> =20 ohm V <sub>GS</sub> =10V <sup>d</sup>		15		ns
t <sub>r</sub>	Turn-On Rise Time			93		ns
t <sub>D(OFF)</sub>	Turn-Off Delay Time			85		ns
t <sub>f</sub>	Turn-Off Fall Time			85		ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =200V, I <sub>D</sub> =10A, V <sub>GS</sub> =10V <sup>d</sup>		29.4		nC
Q <sub>gs</sub>	Gate-Source Charge			4.2		nC
Q <sub>gd</sub>	Gate-Drain("Miller") Charge			15.75		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
I <sub>S</sub>	Maximum Continuous Source Current(Body Diode)				10	A
I <sub>SM</sub>	Maximum Pulsed Source Current(Body Diode)				40	A
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> =0V, I <sub>S</sub> =5A <sup>d</sup>			1.5	V
<b>Notes :</b>						
a. Repetitive Rating : Pulse width limited by maximum junction temperature.						
b. V <sub>DD</sub> =50V, starting T <sub>J</sub> =25°C, L=6mH, R <sub>G</sub> =25Ω, I <sub>AS</sub> =10A						
c. I <sub>SD</sub> ≤ 10A, di/dt ≤ 100A/us, V <sub>DD</sub> ≤ V <sub>(BR)DSS</sub> , T <sub>J</sub> ≤ 150°C						
d. Pulse Test : Pulse width ≤ 300us, Duty cycle ≤ 2%.						

Jul,22,2009

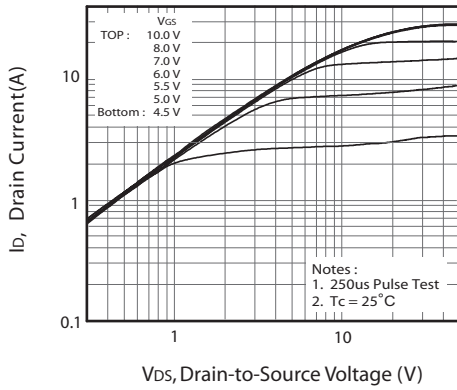


Figure 1. Output Characteristics

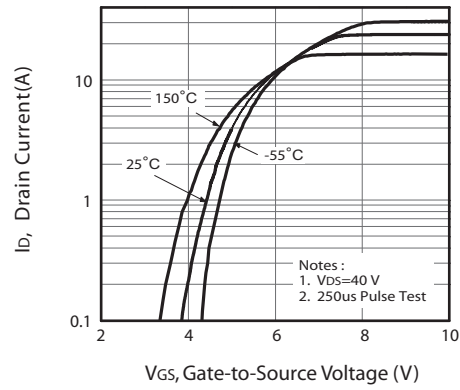


Figure 2. Transfer Characteristics

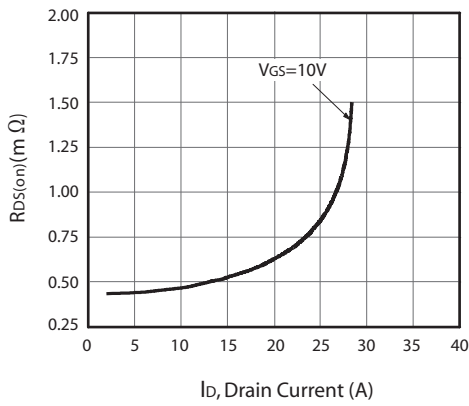


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

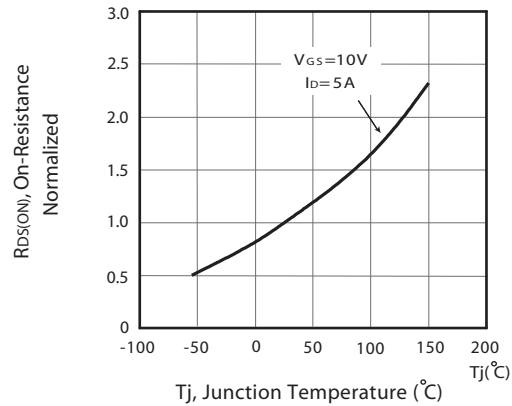


Figure 4. On-Resistance Variation with Drain Current and Temperature

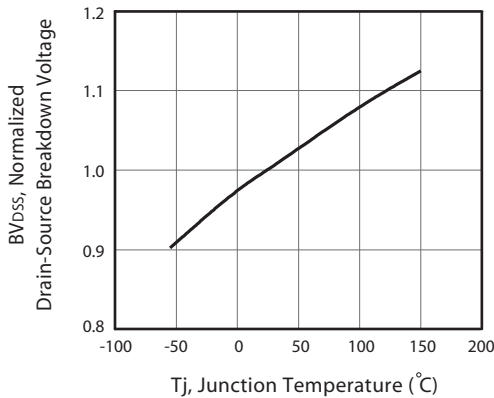


Figure 5. Breakdown Voltage Variation with Temperature

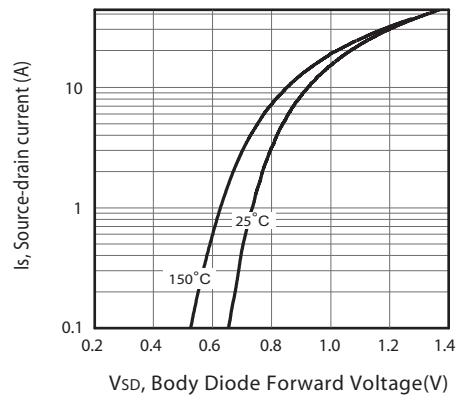
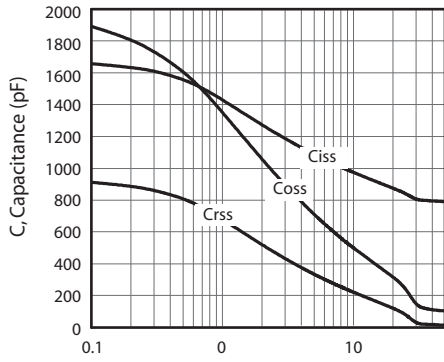
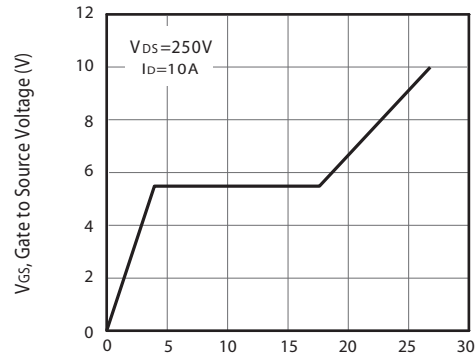


Figure 6. Body Diode Forward Voltage Variation with Source Current



$V_{DS}$ , Drain-to Source Voltage (V)

Figure 7. Capacitance



$Q_g$ , Total Gate Charge (nC)

Figure 8. Gate Charge

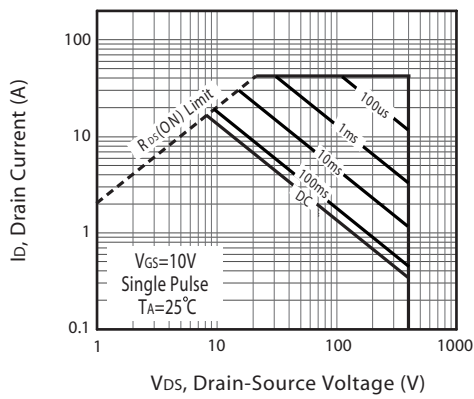


Figure 9. Maximum Safe Operating Area for SDP740

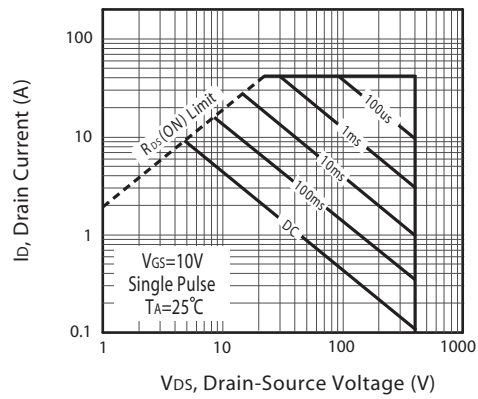
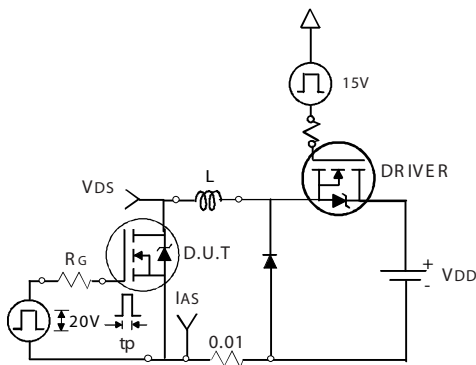
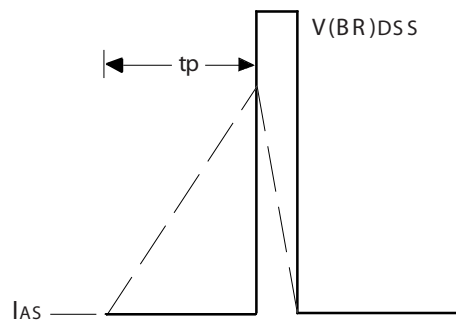


Figure 10. Maximum Safe Operating Area for SDF740



Unclamped Inductive Test Circuit

Figure 11a.



Unclamped Inductive Waveforms

Figure 11b.

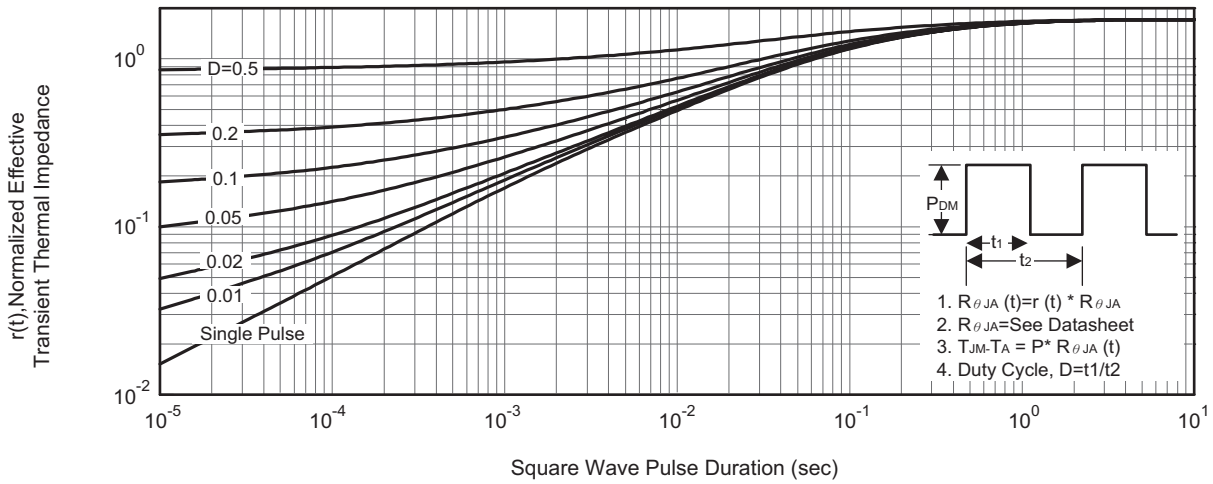


Figure 12.1 Normalized Thermal Transient Impedance Curve for SDP740

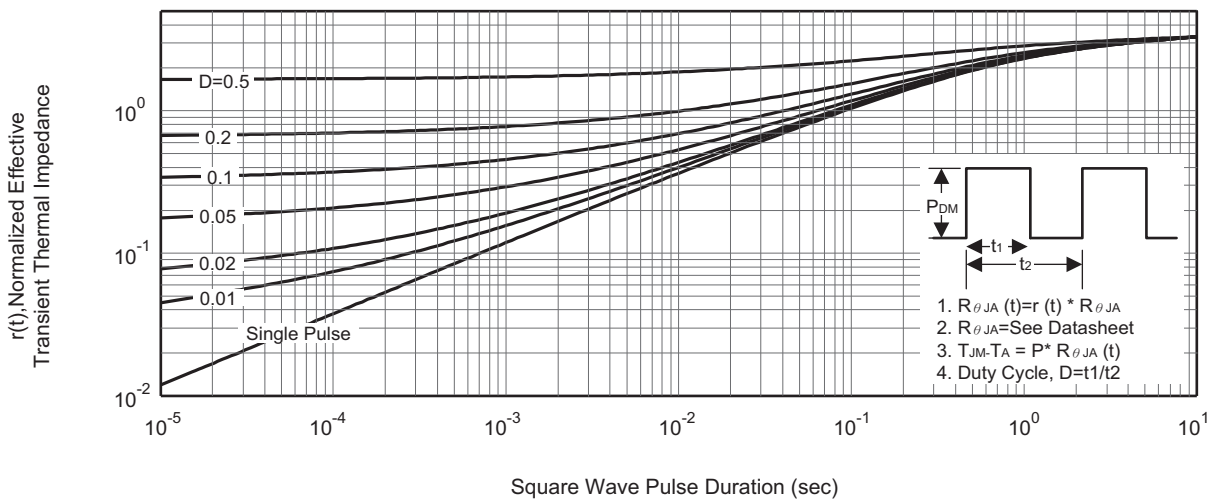
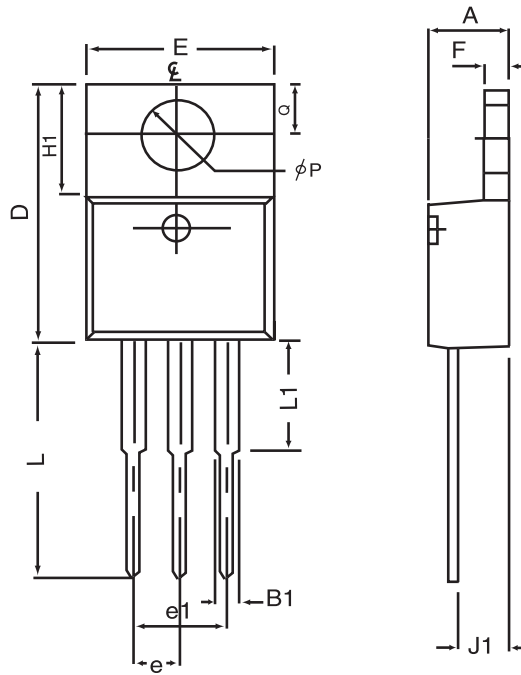


Figure 12.2 Normalized Thermal Transient Impedance Curve for SDF740

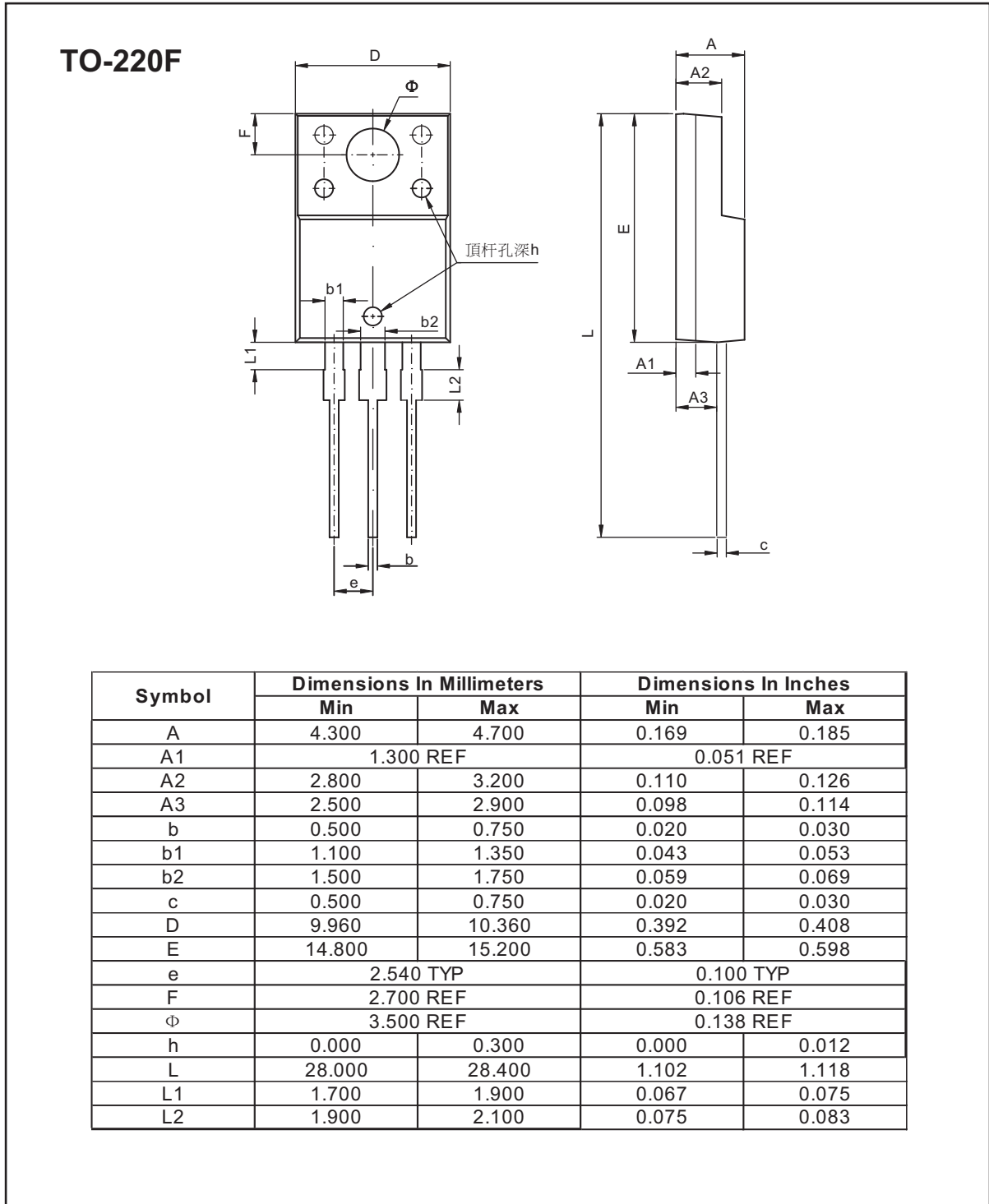
PACKAGE OUTLINE DIMENSIONS

TO-220



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.32	4.80	0.170	0.189
B1	1.27	1.65	0.050	0.630
D	14.6	16.00	0.575	0.610
E	9.70	10.41	0.382	0.410
e	2.34	2.74	0.092	0.108
e1	4.68	5.48	0.184	0.216
F	1.14	1.40	0.045	0.055
H1	5.97	6.73	0.235	0.265
J1	2.20	2.79	0.087	0.110
L	12.88	14.22	0.507	0.560
L1	3.00	6.35	0.120	0.250
phi P	3.50	3.94	0.138	0.155
Q	2.54	3.05	0.100	0.120

## PACKAGE OUTLINE DIMENSIONS



## TO-220/220F Tube

